Comments and Corrections

Corrections to "*In Situ* Oxide, GaN Interlayer-Based Vertical Trench MOSFET (OG-FET) on Bulk GaN Substrates"

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In the above paper [1], the fifth author's name was printed incorrectly. The correct name is Junqian Liu.

REFERENCES

[1] C. Gupta, C. Lund, S. H. Chan, A. Agarwal, J. Liu, Y. Enatsu, S. Keller, and U. K. Mishr, "*In situ* oxide, GaN interlayer-based vertical trench MOSFET (OG-FET) on bulk GaN substrates," *IEEE Electron Device Lett.*, vol. 38, no. 3, pp. 353–355, Mar. 2017.

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